TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# ТРСС8006-Н

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q<sub>SW</sub> = 7.4 nC (typ.)
- Low drain-source ON-resistance:

 $\mathsf{R}_{\mathsf{DS}\;(\mathsf{ON})}$  = 6.5 m $\Omega$  (typ.) (  $\mathsf{V}_{\mathsf{GS}}$  = 4.5 V)

- High forward transfer admittance:  $|Y_{fs}| = 67 \text{ S} (typ.)$
- Low leakage current:  $I_{DSS}$  = 10  $\mu$ A (max) (V<sub>DS</sub> = 30 V)
- Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.2 mA)

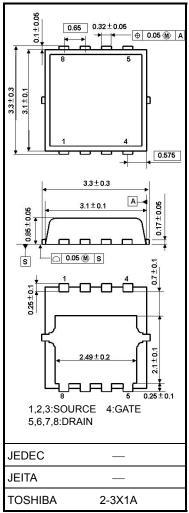
Absolute Maximum Ratings (Ta = 25°C)

Characte	ristic	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	30	V	
Drain-gate voltage (R	GS = 20 kΩ)	V <sub>DGR</sub>	30	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	ID	22	А	
Drain current	Pulsed (Note 1)	I <sub>DP</sub>	66	A	
Drain power dissipati	on (Tc = 25°C)	5°C) P <sub>D</sub> 27			
Drain power dissipation (t = 10 s) (Note 2a)		PD	1.9	W	
Drain power dissipation (t = 10 s) (Note 2b)		PD	0.7	W	
Single-pulse avalancl	ne energy (Note 3)	E <sub>AS</sub>	126	mJ	
Avalanche current		I <sub>AR</sub>	22	А	
Repetitive avalanche (To	energy = 25°C) (Note 4)	E <sub>AR</sub>	1.89	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C	

Note: For Notes 1 to 4, refer to the next page.

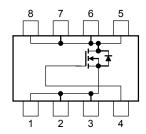
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.02 g (typ.)

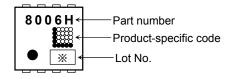
#### **Circuit Configuration**



#### **Thermal Characteristics**

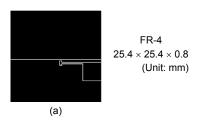
Characteristic	Symbol	Max	Unit	
Thermal resistance, channel to case (Tc = 25°C)	R <sub>th (ch-c)</sub>	4.7	°C/W	
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	66	°C/W	
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	180	°C/W	

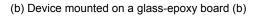
#### Marking (Note 5)

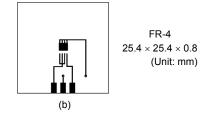


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)







- Note 3: V\_DD = 24 V, T\_{ch} = 25 ^{\circ}C (initial), L = 200  $\mu$ H, R\_G = 25  $\Omega$ , I<sub>AR</sub> = 22 A
- Note 4: Repetitive rating: pulse width limited by maximum channel temperature
- Note 5: \* Weekly code: (Three digits)



Week of manufacture (01 for the first week of the year, continuing up to 52 or 53)

Year of manufacture (The last digit of the year)

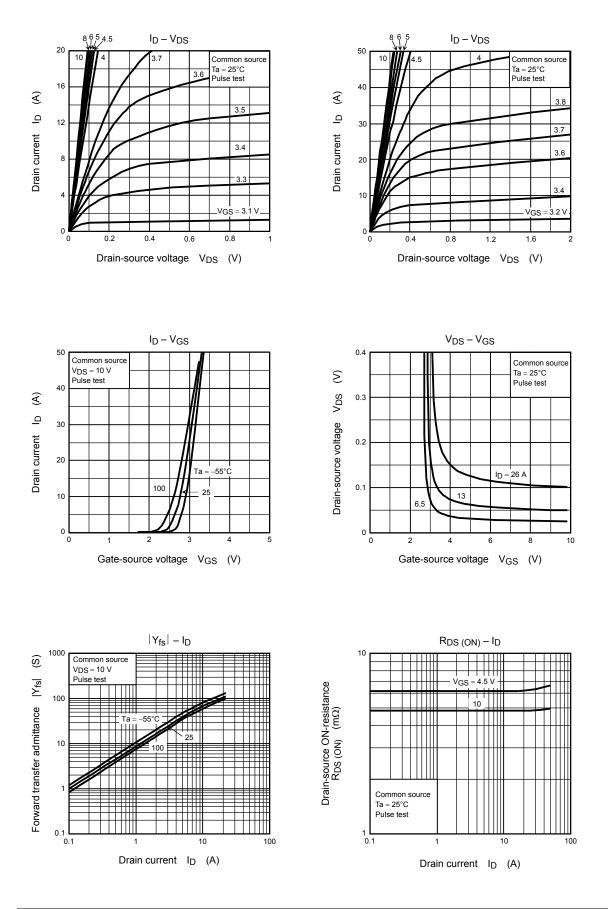
#### **Electrical Characteristics (Ta = 25°C)**

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS}=\pm 20~V,~V_{DS}=0~V$		—	±100	nA	
Drain cutoff curre	nt	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	_	10	μA	
Drain agurag broakdawn voltaga		V (BR) DSS	$I_D=10\ mA,\ V_{GS}=0\ V$	30	_	_	V	
Dialit-source brea	n-source breakdown voltage		$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_	_	v	
Gate threshold vo	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.2 \text{ mA}$	1.3	_	2.3	V	
Drain-source ON-resistance		Pro (ou)	$V_{GS} = 4.5 \text{ V}, I_D = 11 \text{ A}$		6.5	9.3		
Drain-source ON	resistance	R <sub>DS</sub> (ON)	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 11 \text{ A}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	mΩ			
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 11 \text{ A}$	34	67	_	S	
Input capacitance	è	C <sub>iss</sub>		_	1700	2200	pF	
Reverse transfer	capacitance	C <sub>rss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$	_	110	180		
Output capacitance		C <sub>oss</sub>			350	_		
Gate resistance		rg	$V_{DS}=10~V,~V_{GS}=0~V,~f=5~MHz$	2.8 4.2		4.2	Ω	
Switching time	Rise time	tr	$V_{GS} \stackrel{10}{}_{0}V \prod I_{D} = 11 \text{ A}$	_	3.8	_	ns	
	Turn-on time	t <sub>on</sub>		_	10	_		
	Fall time	t <sub>f</sub>		_	9.7	_		
	Turn-off time	t <sub>off</sub>	$V_{DD} \approx 15 \text{ V}$ Duty $\leq 1\%$ , t <sub>W</sub> = 10 µs	_	42	_		
Total gate charge	Total gate charge (gate-source plus gate-drain)		$V_{DD} \approx 24 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 22 \text{ A}$		27	_		
(gate-source plus			$V_{DD}\approx 24~V,~V_{GS}=5~V,~I_{D}=22~A$		15			
Gate-source charge 1		Q <sub>gs1</sub>	$V_{DD}\approx 24~V,~V_{GS}=10~V,~I_{D}=22~A$		5.2	_	nC	
Gate-drain ("Miller") charge		Q <sub>gd</sub>			4.8			
Gate switch charge		Q <sub>SW</sub>	]	_	7.4	_		

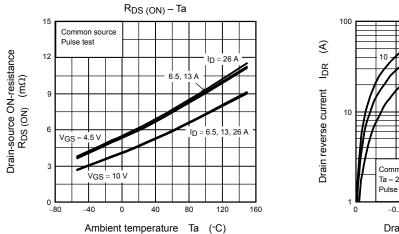
#### Source-Drain Ratings and Characteristics (Ta = 25°C)

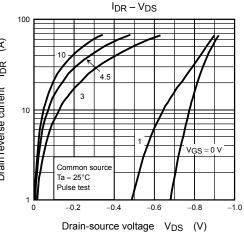
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	—	_	_	66	А
Forward voltage (diode)			VDSF	$I_{DR}=22~A,~V_{GS}=0~V$	_	_	-1.2	V

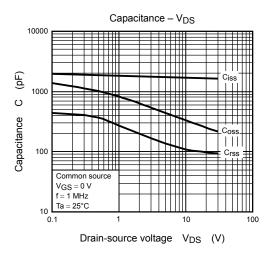
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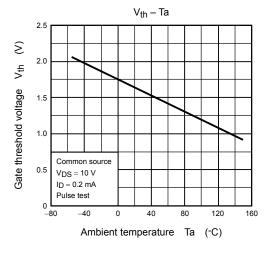


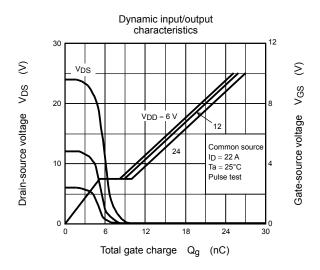
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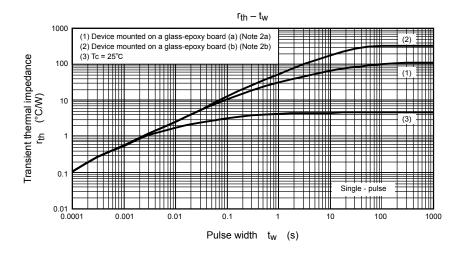


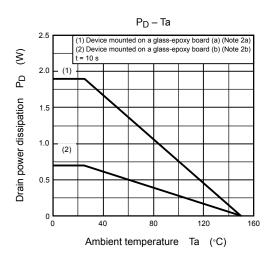


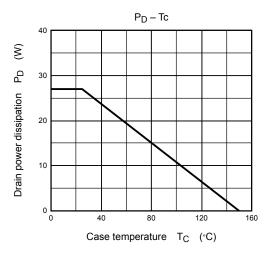


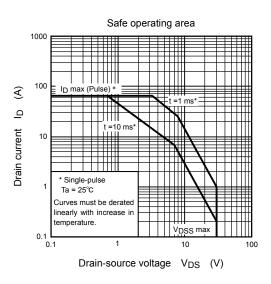












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